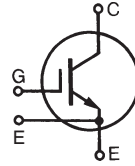


650V XPT™ IGBT GenX3™

IXYN100N65A3

Ultra Low-V_{sat} PT IGBT
for up to 5kHz Switching

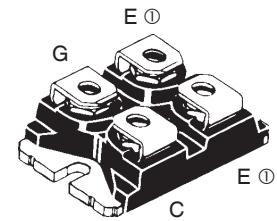


$$\begin{aligned} V_{CES} &= 650V \\ I_{C110} &= 100A \\ V_{CE(sat)} &\leq 1.80V \\ t_{fi(typ)} &= 122ns \end{aligned}$$

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 175°C	650	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 175°C , $R_{GE} = 1M\Omega$	650	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	170	A
I_{C110}	$T_C = 110^\circ\text{C}$	100	A
I_{CM}	$T_C = 25^\circ\text{C}$, 1ms	460	A
I_A	$T_C = 25^\circ\text{C}$	50	A
E_{AS}	$T_C = 25^\circ\text{C}$	600	mJ
SSOA (RBSOA)	$V_{GE} = 15V$, $T_{VJ} = 150^\circ\text{C}$, $R_G = 2\Omega$ Clamped Inductive Load	$I_{CM} = 200$ $V_{CE} \leq V_{CES}$	A
t_{sc} (SCSOA)	$V_{GE} = 15V$, $V_{CE} = 360V$, $T_J = 150^\circ\text{C}$ $R_G = 82\Omega$, Non Repetitive	8	μs
P_C	$T_C = 25^\circ\text{C}$	600	W
T_J		-55 ... +175	$^\circ\text{C}$
T_{JM}		175	$^\circ\text{C}$
T_{stg}		-55 ... +175	$^\circ\text{C}$
V_{ISOL}	50/60Hz $I_{ISOL} \leq 1mA$	$t = 1min$ $t = 1s$	2500 3000 V~ V~
M_d	Mounting Torque Terminal Connection Torque	1.5/13 1.3/11.5	Nm/lb.in Nm/lb.in
Weight		30	g

SOT-227B, miniBLOC

E153432



G = Gate, C = Collector, E = Emitter
either emitter terminal can be used as
Main or Kelvin Emitter

Features

- Optimized for Low Conduction Losses
- miniBLOC, with Aluminium Nitride Isolation
- International Standard Package
- Isolation Voltage 2500V~
- Optimized for up to 5kHz Switching
- Square RBSOA
- Avalanche Rated
- Short Circuit Capability
- High Current Handling Capability

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

- UPS
- Motor Drives
- SMPS
- Battery Chargers
- Low Frequency Power Inverters

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu\text{A}$, $V_{GE} = 0V$	650		V
$V_{GE(th)}$	$I_C = 250\mu\text{A}$, $V_{CE} = V_{GE}$	3.5		6.0 V
I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0V$ $T_J = 150^\circ\text{C}$			25 μA 500 μA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 200 nA
$V_{CE(sat)}$	$I_C = 70A$, $V_{GE} = 15V$, Note 1 $T_J = 150^\circ\text{C}$		1.44 1.62	V V

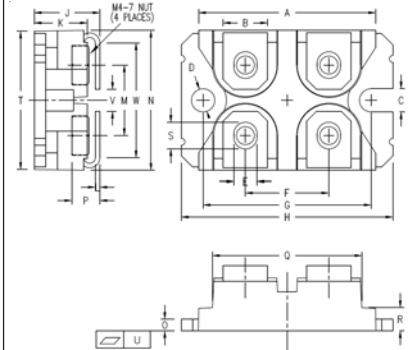
Symbol Test Conditions

($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)

Characteristic Values

		Min.	Typ.	Max.	
g_{fs}	$I_C = 60\text{A}, V_{CE} = 10\text{V}$, Note 1	32	52		S
C_{ies}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		4920		pF
C_{oes}			290		pF
C_{res}			100		pF
$Q_{g(on)}$	$I_C = 70\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		166		nC
Q_{ge}			35		nC
Q_{gc}			73		nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = 50\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 2\Omega$ Note 2		30		ns
t_{ri}			39		ns
E_{on}			2.0		mJ
$t_{d(off)}$			155		ns
t_{fi}			122		ns
E_{off}			1.6		mJ
$t_{d(on)}$	Inductive load, $T_J = 150^\circ\text{C}$ $I_C = 50\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 2\Omega$ Note 2		28		ns
t_{ri}			40		ns
E_{on}			2.6		mJ
$t_{d(off)}$			200		ns
t_{fi}			160		ns
E_{off}			2.4		mJ
R_{thJC}				0.25	$^\circ\text{C/W}$
R_{thCS}		0.05			$^\circ\text{C/W}$

SOT-227B miniBLOC (IXYN)



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.240	1.255	31.50	31.88
B	.307	.323	7.80	8.20
C	.161	.169	4.09	4.29
D	.161	.169	4.09	4.29
E	.161	.169	4.09	4.29
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.489	1.505	37.80	38.23
J	.460	.481	11.68	12.22
K	.351	.378	8.92	9.60
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.078	.084	1.98	2.13
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.155	.174	3.94	4.42
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.002	.004	-0.05	0.1
V	.130	.180	3.30	4.57
W	.780	.830	19.81	21.08

Notes:

1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.
2. Switching times & energy losses may increase for higher $V_{CE}(\text{clamp})$, T_J or R_G .

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

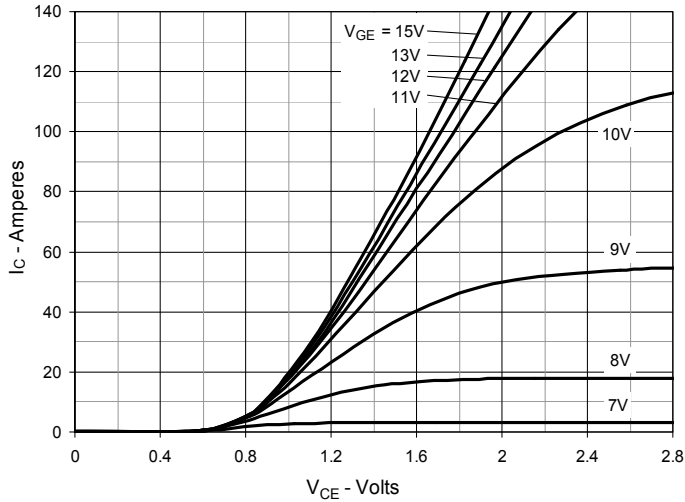
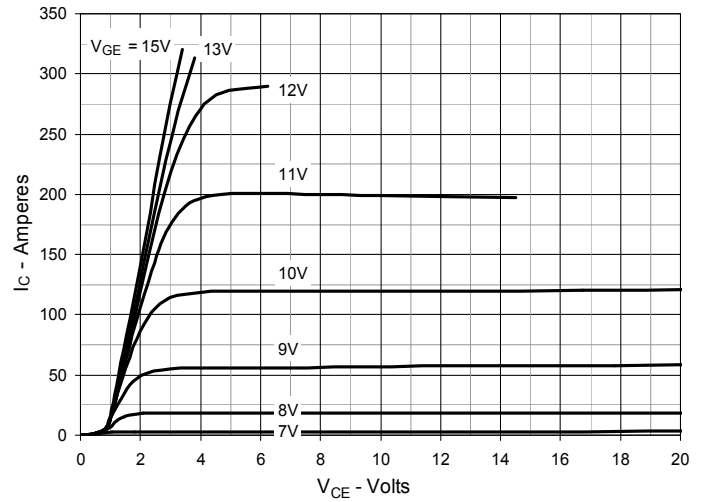
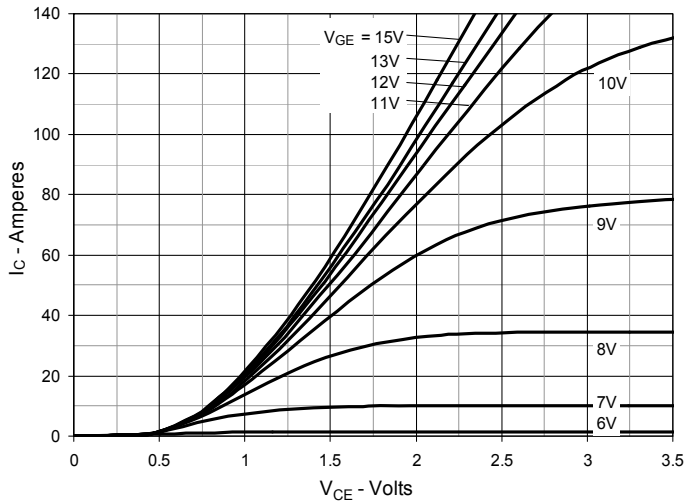
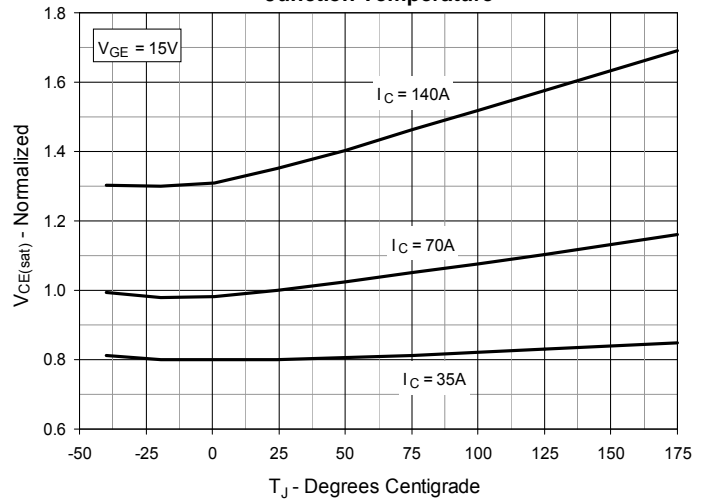
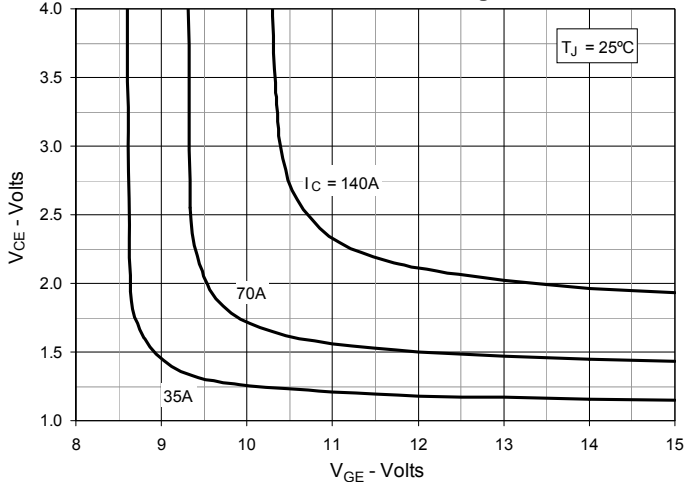
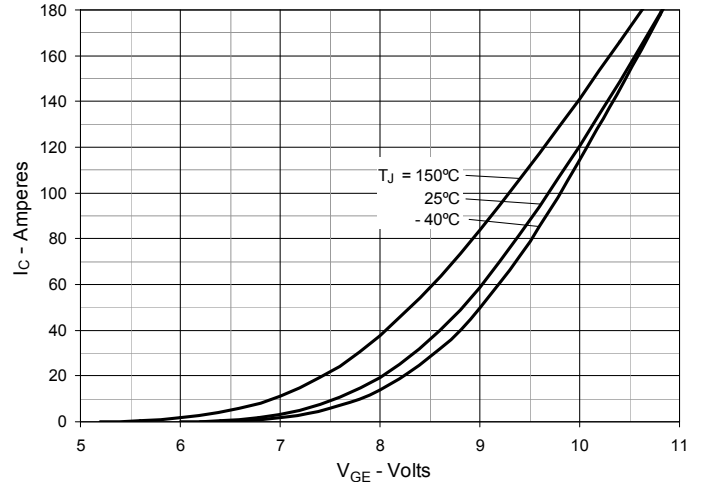
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 3. Output Characteristics @ $T_J = 150^\circ\text{C}$

Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

Fig. 6. Input Admittance


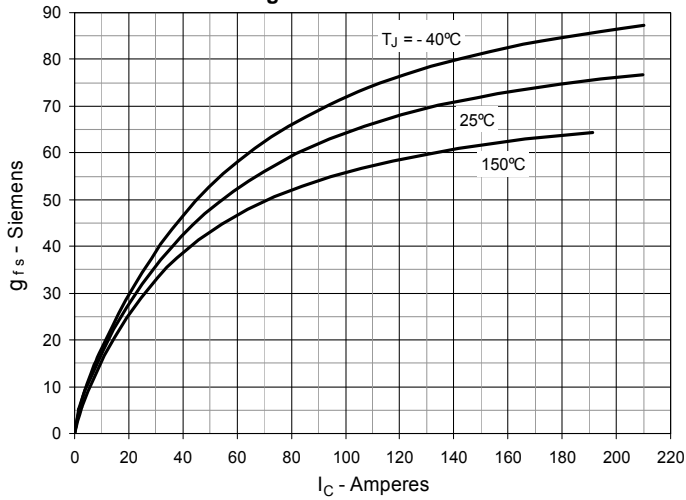
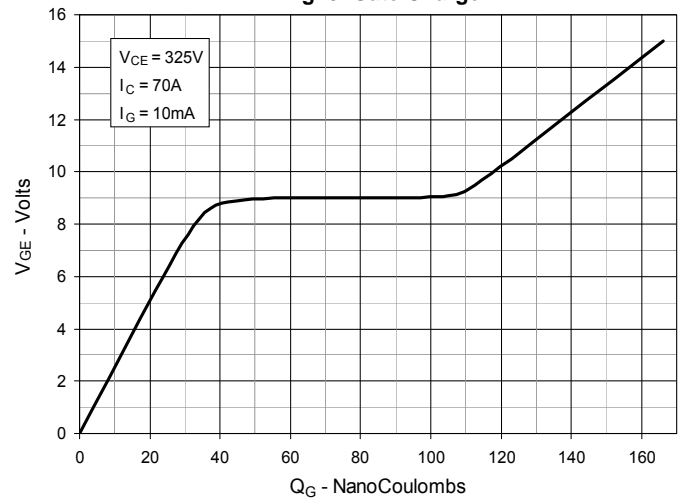
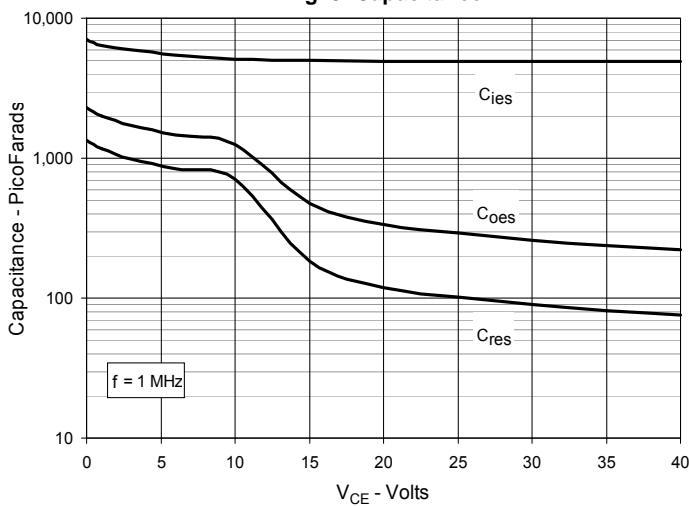
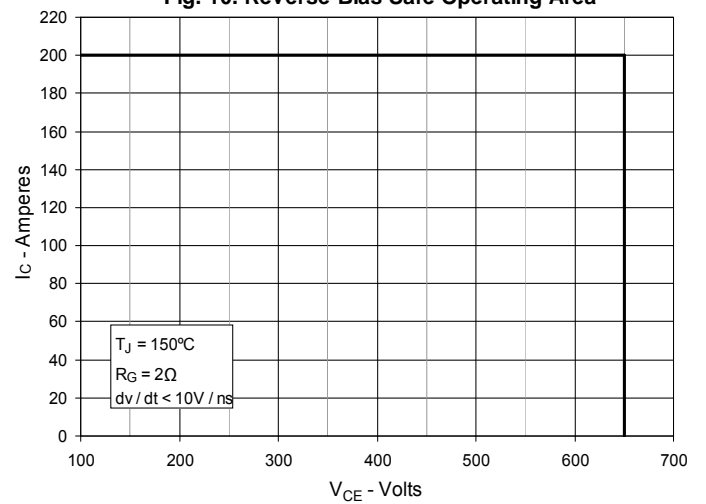
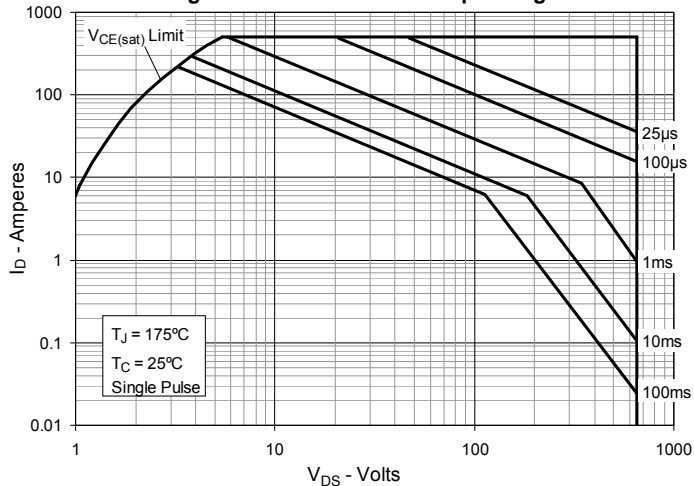
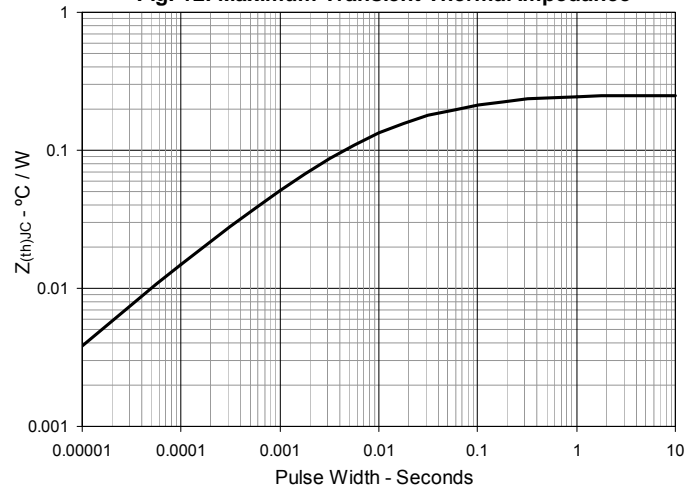
Fig. 7. Transconductance

Fig. 8. Gate Charge

Fig. 9. Capacitance

Fig. 10. Reverse-Bias Safe Operating Area

Fig. 11. Forward-Bias Safe Operating Area

Fig. 12. Maximum Transient Thermal Impedance


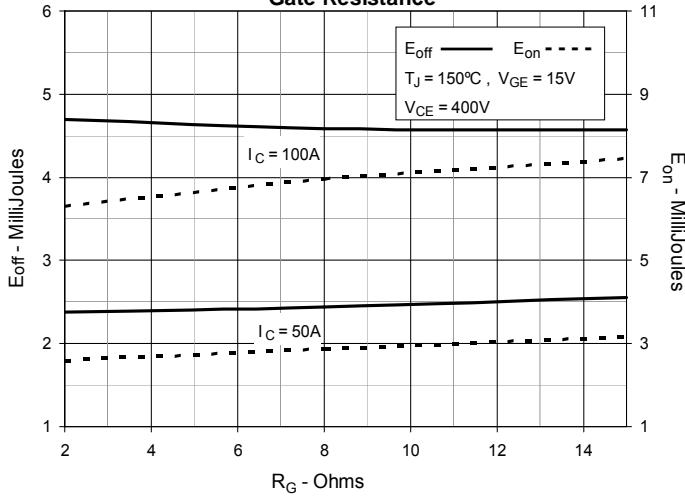
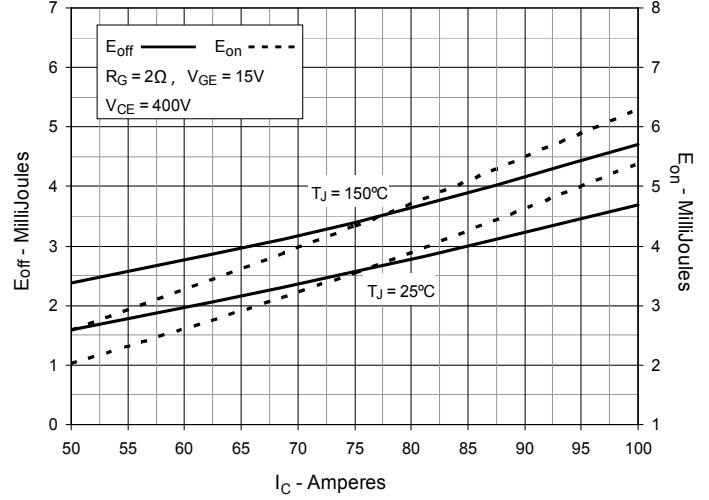
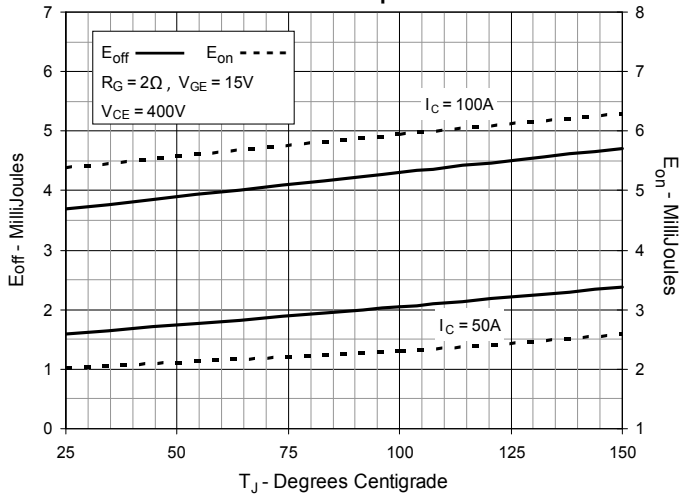
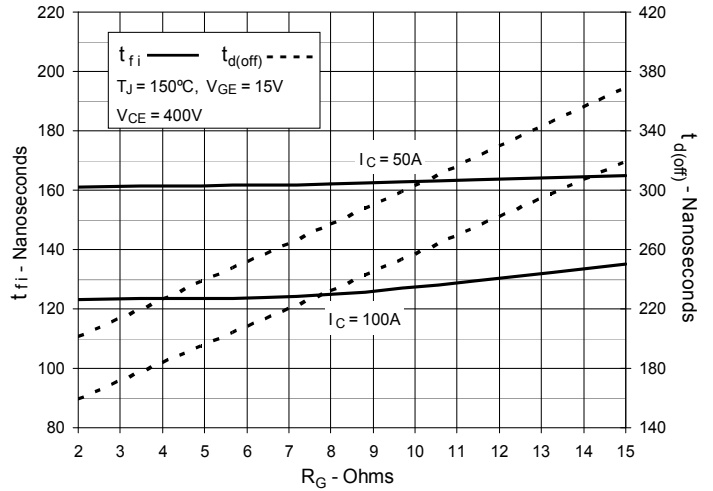
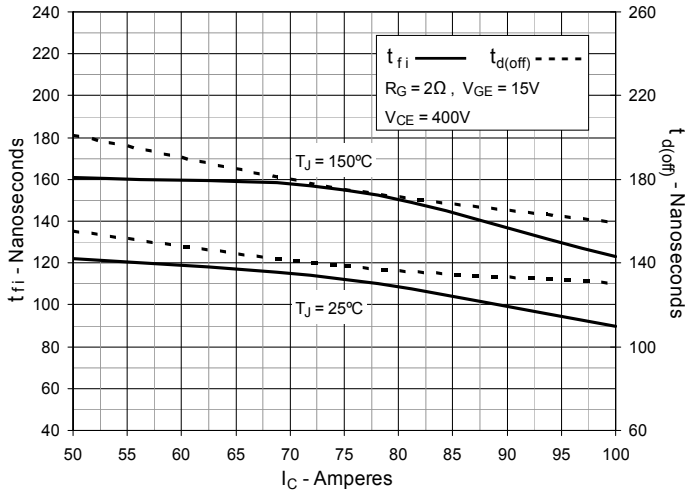
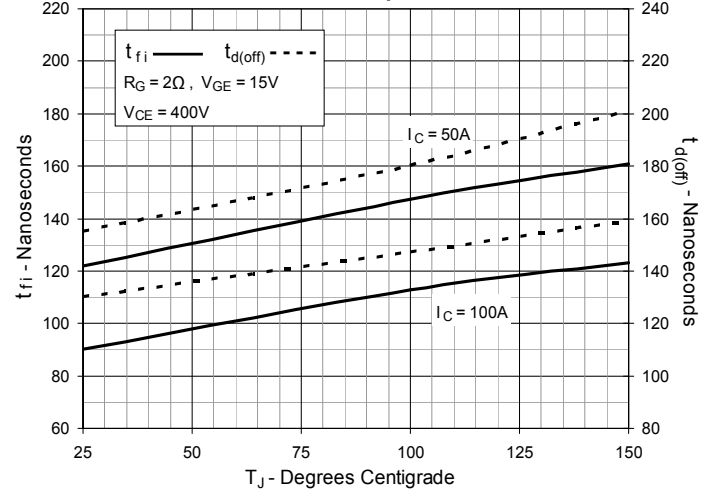
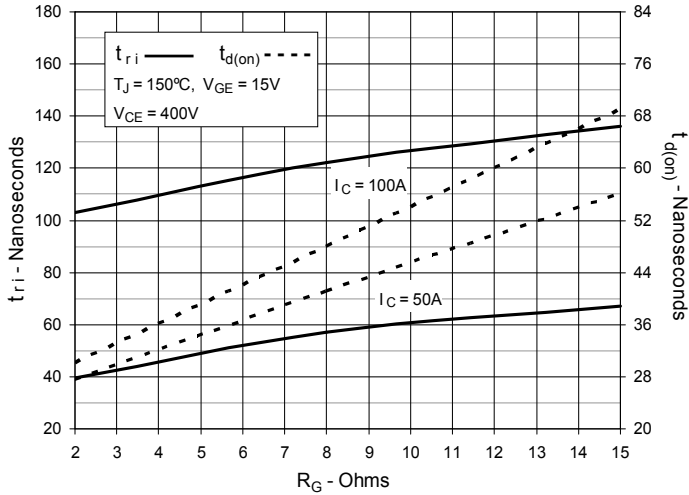
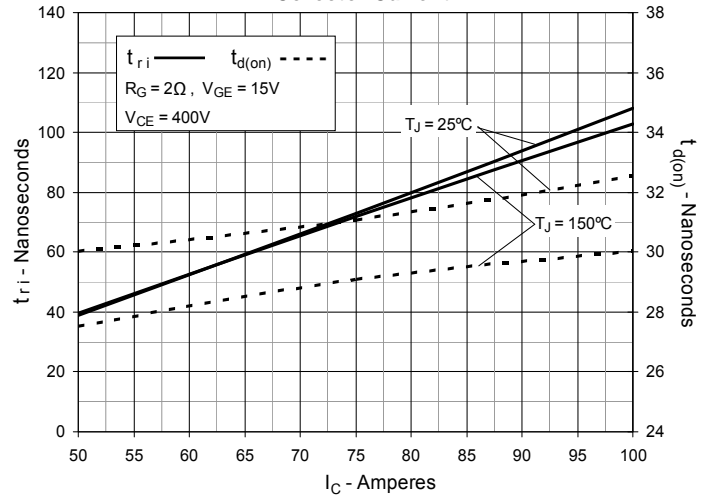
Fig. 13. Inductive Switching Energy Loss vs. Gate Resistance

Fig. 14. Inductive Switching Energy Loss vs. Collector Current

Fig. 15. Inductive Switching Energy Loss vs. Junction Temperature

Fig. 16. Inductive Turn-off Switching Times vs. Gate Resistance

Fig. 17. Inductive Turn-off Switching Times vs. Collector Current

Fig. 18. Inductive Turn-off Switching Times vs. Junction Temperature


Fig. 19. Inductive Turn-on Switching Times vs. Gate Resistance

Fig. 20. Inductive Turn-on Switching Times vs. Collector Current

Fig. 21. Inductive Turn-on Switching Times vs. Junction Temperature
